

Search History (8 pp.) ~~7/20/05~~ (7/20/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	"753103".ap. and (unselect\$3 select\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 15:59
L3	1	"6400604".pn. and eras\$3 near3 chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 16:07
L4	2	"6400604".pn. and (select\$3 unselect\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 16:07
S1	6	"753103".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 15:59
S2	898	"Si.sub."\$4"Ge.sub."\$4	US-PGPUB; USPAT	OR	OFF	2005/07/18 15:27
S3	13	"Si.sub."\$4"Ge.sub."\$4	USPAT	OR	OFF	2005/07/18 15:24
S4	0	magnesium adj fluoromanganate near10 mfg	US-PGPUB; USPAT	OR	OFF	2005/07/18 15:35
S5	0	magnesium adj fluoromanganate	US-PGPUB; USPAT	OR	OFF	2005/07/18 15:28
S6	2371	MFG and magnesium	US-PGPUB; USPAT	OR	OFF	2005/07/18 15:29
S7	2	MFG and magnesium and manganate	US-PGPUB; USPAT	OR	OFF	2005/07/18 15:30
S8	805656	MFG	US-PGPUB; USPAT	OR	ON	2005/07/18 15:30
S9	77943	MFG and manufacturing.ti.	US-PGPUB; USPAT	OR	ON	2005/07/18 15:33
S10	77943	"MFG" and manufacturing.ti.	US-PGPUB; USPAT	OR	ON	2005/07/18 15:32
S11	805656	"MFG"	US-PGPUB; USPAT	OR	ON	2005/07/18 15:32
S12	727713	S11 not S10	US-PGPUB; USPAT	OR	ON	2005/07/18 15:33
S13	311	MFG and manufacturing.ti.	US-PGPUB; USPAT	OR	OFF	2005/07/18 15:33
S14	18628	MFG	US-PGPUB; USPAT	OR	OFF	2005/07/18 15:33

S15	0	magnesium adj (fluoro adj manganate fluoro-manganate) near10 mfg	US-PGPUB; USPAT	OR	OFF	2005/07/18 15:36
S16	48	NAND adj flash.ti.	US-PGPUB; USPAT	OR	OFF	2005/07/18 15:50
S17	143	NAND near2 flash near10 memory. ti,ab,clm.	USPAT	OR	OFF	2005/07/18 17:35
S18	38	NAND near2 flash near10 memory. ti,ab,clm. and floating near2 gate and control near2 gate and select near2 gate and (tunnel tunneling tunnelling Fowler Nordheim)	USPAT	OR	OFF	2005/07/18 17:42
S19	143	NAND near2 flash near10 memory. ti,ab,clm.	USPAT	OR	OFF	2005/07/18 17:47
S20	12	NAND near2 flash near10 memory. ti,ab,clm. and stack near10 gate	USPAT	OR	OFF	2005/07/18 17:48
S21	29	NAND near2 flash near10 memory. ti,ab,clm. and stack near10 gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/18 17:49
S22	9	(US-20040057286-\$ or US-20050133851-\$ or US-20050133860-\$ or US-20050145923-\$).did. or (US-6417538-\$ or US-6573556-\$ or US-6605506-\$ or US-6790729-\$ or US-6885586-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/07/19 08:20
S23	8	((("6,498,377") or ("6,503,785") or ("6,091,104") or ("6115,287") or ("5,197,027") or ("5,541,130") or ("6,034,894") or ("6,747,310")).PN. or (2004/0130947).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/07/19 08:25
S24	2	((("4959812") or ("5050125")).PN.	US-PGPUB; USPAT	OR	OFF	2005/07/19 08:39
S25	0	("2andselectandcontrolandfloating").PN.	US-PGPUB; USPAT	OR	OFF	2005/07/19 08:39
S26	7	S23 and floating and select\$3 and control\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 08:43
S27	2	("4959812").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 08:49

S28	4351	select near10 (floating control) near10 (surround\$3 side adjacent "next") and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 08:51
S29	1049	select near10 (floating control) near10 (surround\$3 side adjacent "next") and memory and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 08:51
S30	230	select near10 (floating control) near10 (surround\$3 side adjacent "next") and memory and flash and nand	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 08:52
S31	163	select near10 (floating control) near10 (surround\$3 side adjacent "next") and memory and flash and nand and tunnel\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 08:57
S32.	5	"223208".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 09:04
S33	8411	((257/314) or (257/315) or (257/316) or (257/319) or (257/321) or (257/323) or (257/326) or (365/185.05) or (365/185.11) or (365/185.17) or (365/63)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 14:32
S34	1582	S33 and select near10 (control floating)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 09:07
S35	1001	S33 and select near10 (control floating) and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 09:07
S36	932	S33 and select near10 (control floating) and flash and voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 09:12
S37	849	S33 and select near6 (control floating) and flash and voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 09:14

S38	223	S33 and select near6 (control floating) and flash near2 nand and voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 09:36
S39	4	((("6370081") or ("6400604")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 12:46
S40	2	"20010017789"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 09:45
S41	510	(flotox tunnel\$4) and select near8 (control floating) near8 ("side" surround\$3 adjacent "next")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 09:46
S42	1516	source adj (region diffusion contact) near10 overlap\$4 near10 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 12:46
S43	502	(flotox tunnel\$4) and select near8 (control floating) near8 ("side" surround\$3 adjacent "next") and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 12:47
S44	36	S42 and S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 13:01
S45	17	S42 and S43 and overlap\$4 near4 select	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 13:07
S46	71	select adj gate near6 source near6 (directly below "under" underneath overlap\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 13:13
S47	54	select adj gate near4 source near4 (directly below "under" underneath overlap\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 13:14

S48	36	select adj gate near3 source near3 (directly below "under" underneath overlap\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 13:52
S49	1	actrans.as. and select adj gate near4 overlap\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 13:53
S50	1	actrans.as. and select adj gate near8 overlap\$4 near8 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 13:54
S51	20	actrans.as. and select adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 13:59
S53	22	(overlap overlaps overlapping) near10 select adj gate near10 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 14:09
S54	23	(overlap overlaps overlapping) near10 select adj gate near10 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:10
S55	22	(overlap overlaps overlapping) near5 select adj gate near5 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:10
S56	20	(overlap overlaps overlapping) near3 select adj gate near3 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:11
S57	0	(overlap overlaps overlapping) near2 select adj gate near2 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:11
S58	10	(overlap overlaps overlapping) near3 select adj gate near2 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:20

S59	3319	(overlap overlaps overlapping) near3 gate near2 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:20
S60	117	(overlap overlaps overlapping) near3 gate near2 (source drain) near8 (speed voltage) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:25
S61	0	(overlap overlaps overlapping) near3 select adj gate near2 (source drain) near8 (speed voltage) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:26
S62	0	(overlap overlaps overlapping) near3 select near2 gate near2 (source drain) near8 (speed voltage) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:26
S63	2	(overlap overlaps overlapping) near6 select near2 gate near6 (source drain) near8 (speed voltage) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/19 14:26
S64	9294	((257/314) or (257/315) or (257/316) or (257/319) or (257/321) or (257/323) or (257/326) or (365/185.05) or (365/185.11) or (365/185.17) or (365/185.33) or (365/63)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 14:33
S65	1264	(365/185.33).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/07/19 14:33
S66	71	S65 and select adj gate near4 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 15:09
S67	83	S65 and (access select selection second) adj gate near4 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 15:10
S68	53	S65 and (access select selection second) adj gate near8 (source drain) near8 (voltage speed time)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 15:18

S69	2	("6885586").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 15:18
S70	4	((("6815760") or ("6821847")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 15:58
S71	34	source near4 self-align\$4 and NAND adj flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/19 15:59
S72	11	"6400604"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 10:33
S73	2	("6400604").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 16:03
S74	2413	memory adj block.ti,ab,clm. and array and block	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 10:46
S75	398	memory adj block.ti,ab,clm. and array and block and erase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 10:46
S76	81	erase near6 memory adj block.ti, ab,clm. and array and block and erase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 10:52
S77	54	erase near6 memory adj block.ti, ab,clm. and array near4 block and erase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 10:53
S78	24	erase near6 memory adj block.ti, ab,clm. and array near4 block near4 erase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 10:54

S79	6	"753103".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 10:56
S80	56	eras\$3 near3 simultaneous\$2 near6 array and NAND near4 flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 10:57
S81	30	eras\$3 near3 simultaneous\$2 near3 array and NAND adj flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 13:57
S82	42	modulation-doped.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 13:57